



SPP3481

P-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPP3481 is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

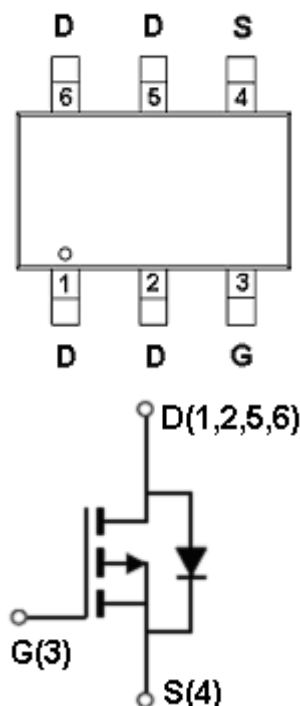
FEATURES

- ◆ -30V/-5.2A, $R_{DS(ON)} = 55m\Omega @ V_{GS} = -10V$
- ◆ -30V/-4.2A, $R_{DS(ON)} = 75m\Omega @ V_{GS} = -4.5V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ TSOP-6P package design

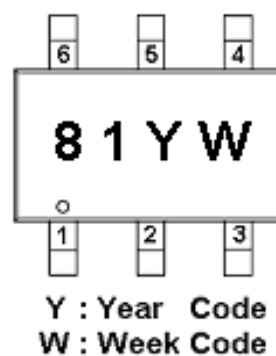
APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

PIN CONFIGURATION(TSOP-6P)



PART MARKING





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PIN DESCRIPTION

Pin	Symbol	Description
1	D	Drain
2	D	Drain
3	G	Gate
4	S	Source
5	D	Drain
6	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPP3481ST6RG	TSOP-6P	81YW
SPP3481ST6RGB	TSOP-6P	81YW

※ Week Code : A ~ Z(1 ~ 26) ; a ~ z(27 ~ 52)

※ SPP3481ST6RG : Tape Reel ; Pb – Free

※ SPP3481ST6RGB : Tape Reel ; Pb – Free; Halogen – Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	-30	V
Gate –Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	-5.2	A
		-4.2	
Pulsed Drain Current	I _{DM}	-20	A
Continuous Source Current(Diode Conduction)	I _S	-1.7	A
Power Dissipation	P _D	2.0	W
		1.3	
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	90	°C/W



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ELECTRICAL CHARACTERISTICS

(T_A=25°C Unless otherwise noted)

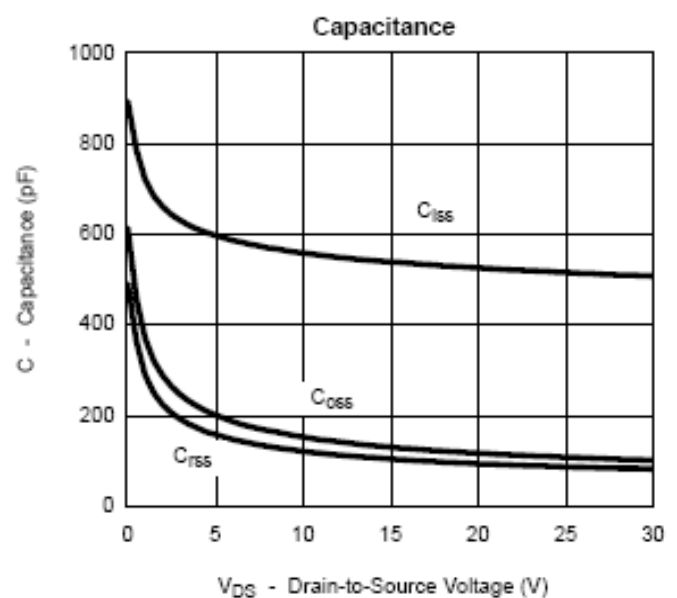
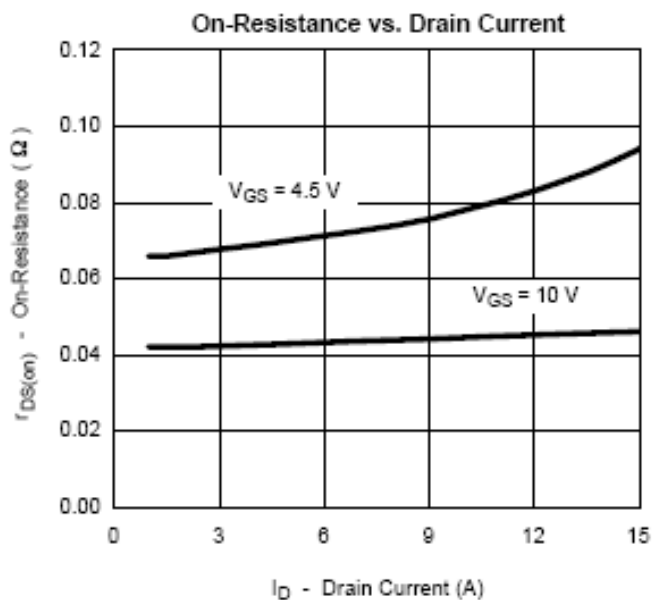
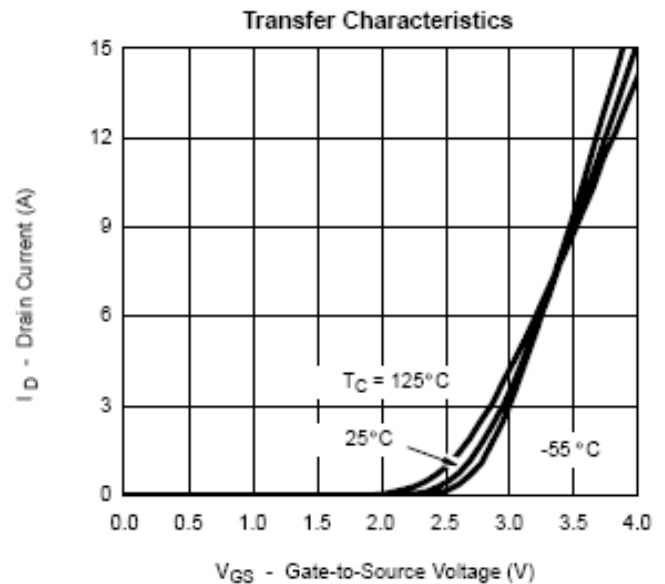
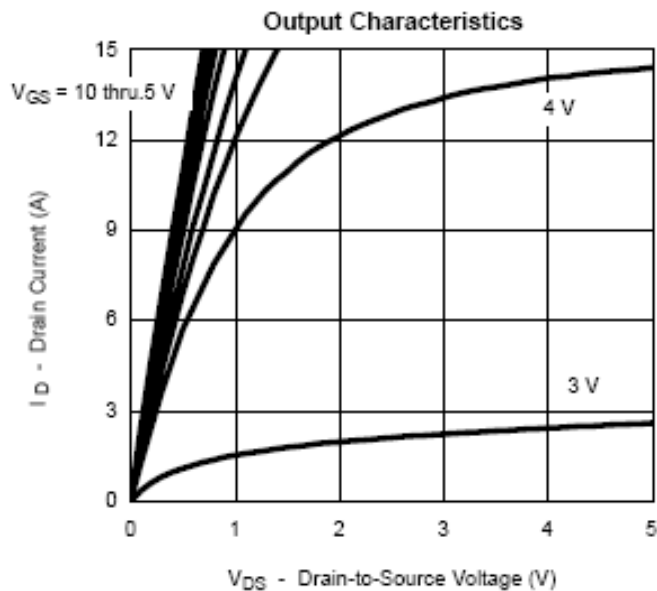
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250uA	-30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1.0		-3.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-21V, V _{GS} =0V			-2	uA
		V _{DS} =-21V, V _{GS} =0V T _J =55°C			-10	
On-State Drain Current	I _{D(on)}	V _{DS} ≤ -5V, V _{GS} =-10V	-10			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-5.2A		0.042	0.055	Ω
		V _{GS} =-4.5V, I _D =-4.2A		0.058	0.075	
Forward Transconductance	g _{fs}	V _{DS} =-5.0V, I _D =-4.0A		10		S
Diode Forward Voltage	V _{SD}	I _S =-1.0A, V _{GS} =0V		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =-15V, V _{GS} =-10V I _D =-4.0A		14	21	nC
Gate-Source Charge	Q _{gs}			1.9		
Gate-Drain Charge	Q _{gd}			3.7		
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V f=1MHz		540		pF
Output Capacitance	C _{oss}			131		
Reverse Transfer Capacitance	C _{rss}			105		
Turn-On Time	t _{d(on)}	V _{DD} =-15V, R _L =15Ω I _D =-1.0A, V _{GEN} =-10V R _G =6Ω		10	15	ns
	t _r			15	25	
Turn-Off Time	t _{d(off)}			31	50	
	t _f			20	30	



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TYPICAL CHARACTERISTICS

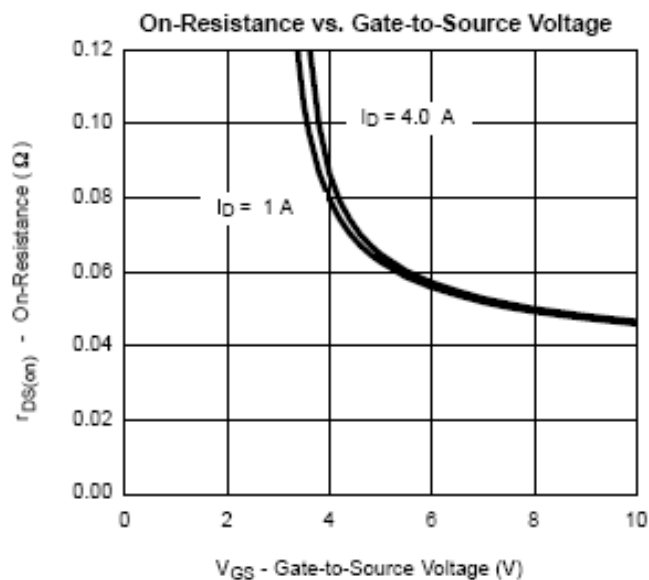
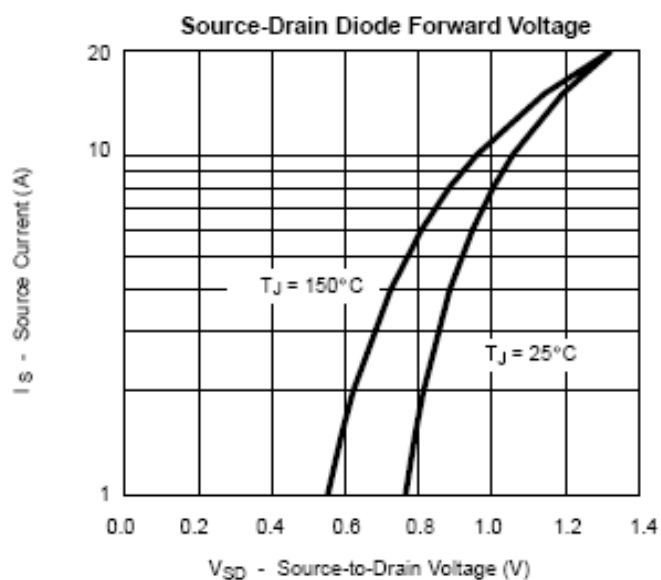
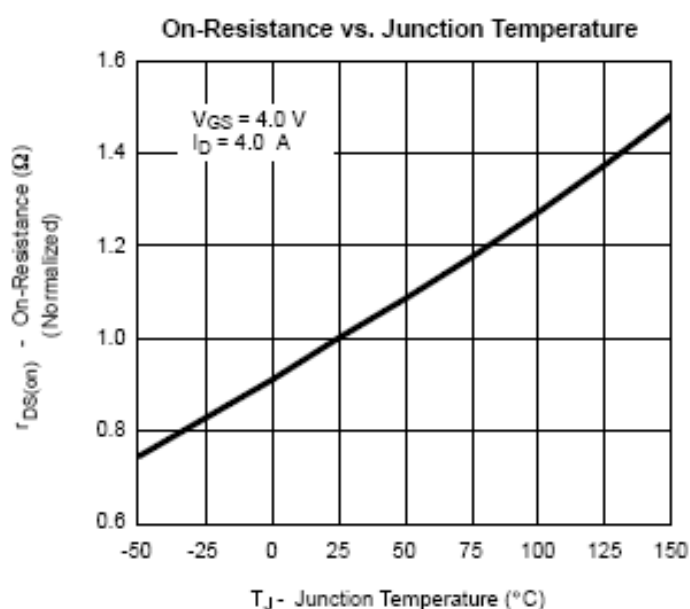
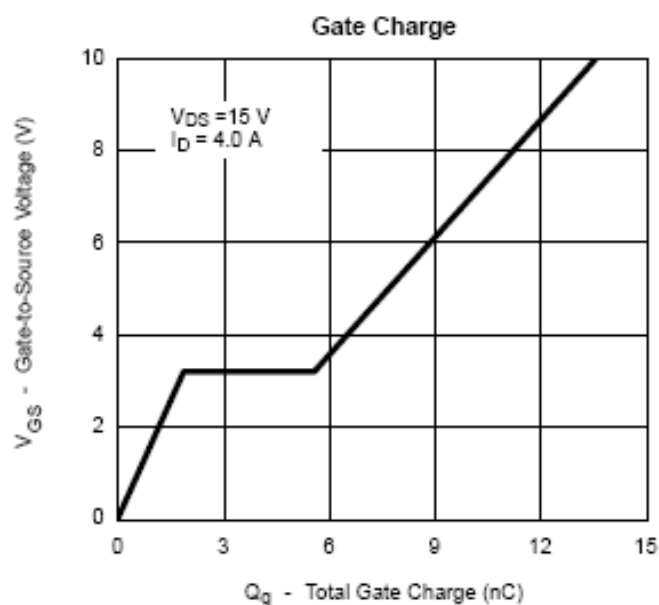




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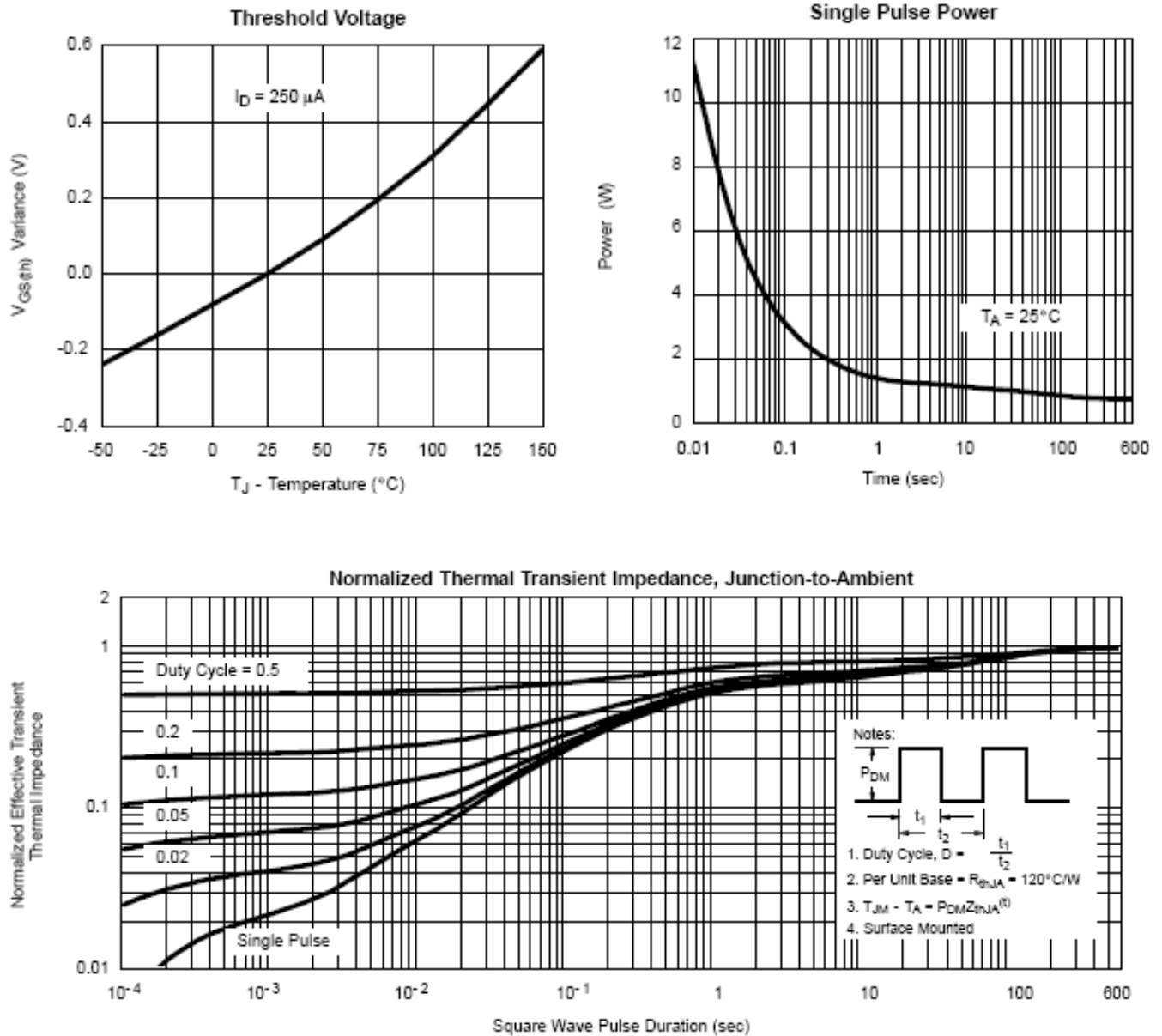




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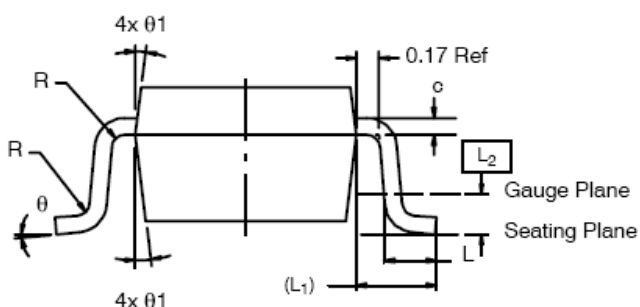
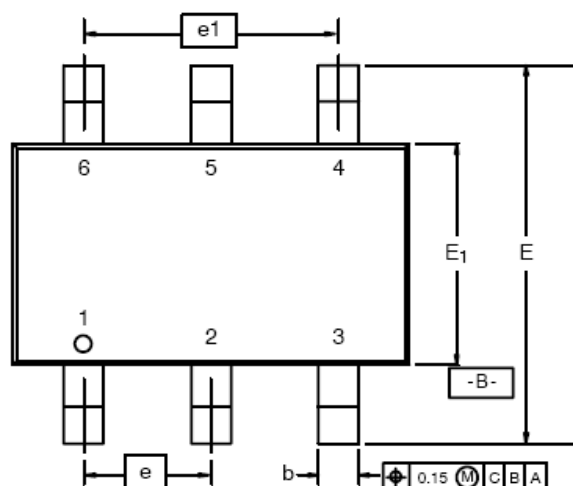




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TSOP- 6P PACKAGE OUTLINE



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	1.00 BSC			0.0394 BSC		
e ₁	1.90	2.00	2.10	0.075	0.080	0.085
L	0.35	-	0.50	0.014	-	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ ₁	7° Nom			7° Nom		



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